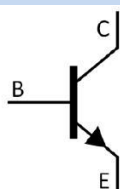


WR0<50 P QSQ Silicon NPN transistor in a TO-92LM Plastic Package.

5VE97 : +D,
Complementary pair with 2SB647(A).

Low frequency power amplifier.



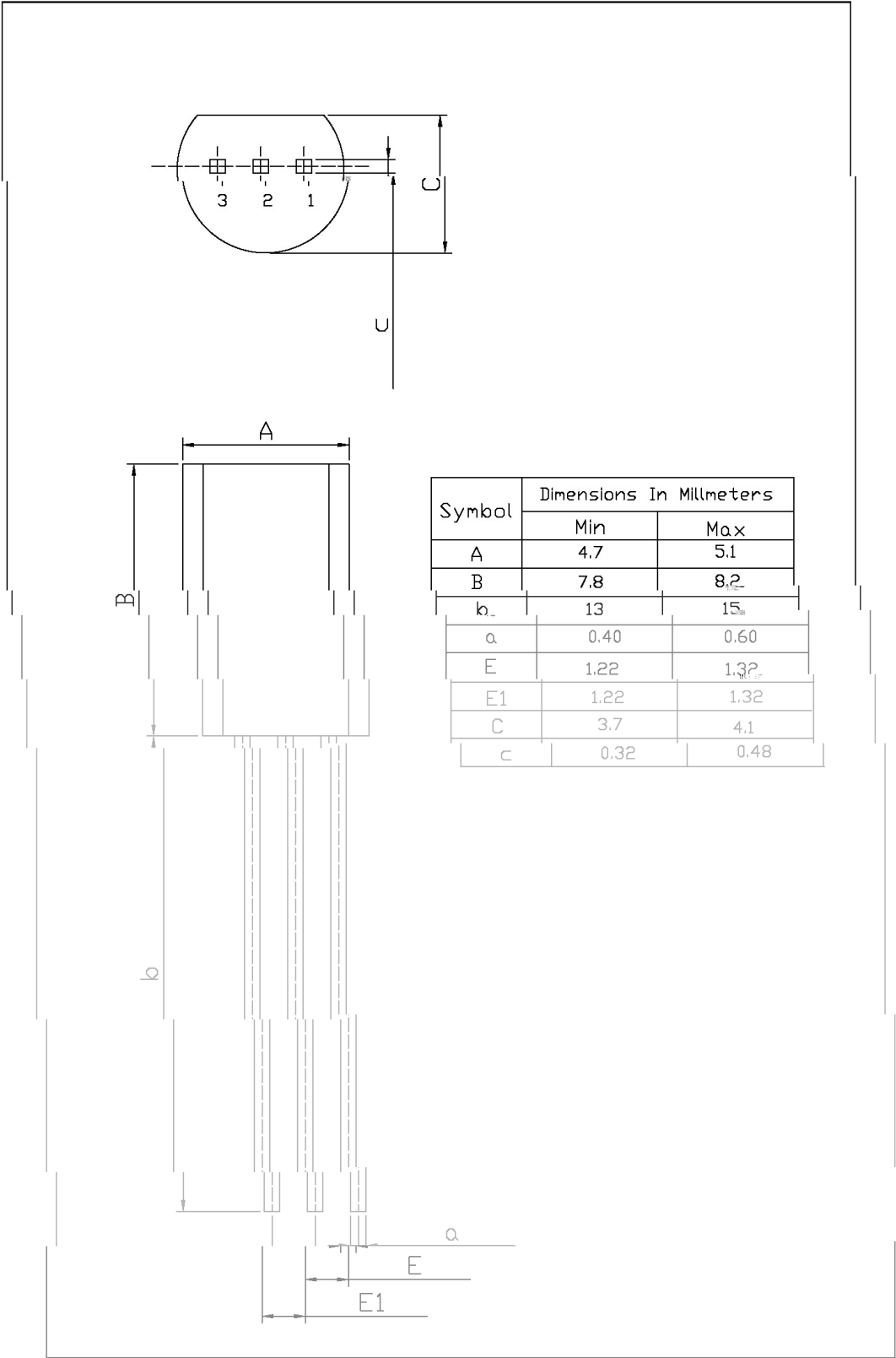
PIN1 Base PIN 2 Collector PIN 3 Emitter

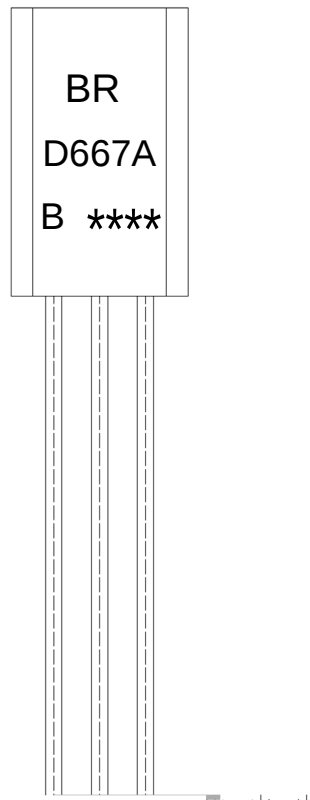
h_{FE} Classifications Symbol	B	C	D
h_{FE} Range	60 120	100 200	160 320

Parameter	Symbol		Rating	Unit
Collector to Base Voltage	V_{CBO}		120	V
Collector to Emitter Voltage	V_{CEO}	2SD667	80	V
		2SD667A	100	
Emitter to Base Voltage	V_{EBO}		5.0	V
Collector Current (DC)	I_C		1.0	A
Collector Current (Pulse)	I_{CP}		2.0	A
Collector Power Dissipation	P_C		900	mW
Junction Temperature	T_j		150	

T0-92LM

Unit: mm





EU:

G99 : D

E: k_{IH}

Note:

BR: Company Code.

D667A: Product Type.

B: h_{FE} Classifications Symbol

****: Lot No. Code,code change with Lot No.



Note:

- | | | | | | |
|---|-----|------|----|----------|---|
| 1 | 25 | 150% | 60 | 90sec; | 1.Preheating:25~150%, Time:60~90sec. |
| 2 | 255 | ±5% | 5 | ±0.5sec; | 2.Peak Temp.:255 ±5%, Duration:5 ±0.5sec. |
| 3 | | | 2 | 10%/sec. | 3. Cooling Speed: 2~10%/sec. |

270 ±5% 10 ±1 sec. Temp.:270±5 Time:10±1 sec

/ BULK

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm3)		
	Units/Bag 只/袋	Bags/Inner Box 袋/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Bag 袋	Inner Box 盒	Outer Box 箱
TO-92LM	1,000	8	8,000	5	40,000	135×190	237×172×102	560×245×195

/ AMMO

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm3)	
	Units/tape 只/纸带	Tape/Inner Box 纸带/盒	Rows/Inner Box 纸带层/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Inner Box 盒	Outer Box 箱
TO-92LM	2,500	1	100	10	25,000	328×230×42	小箱 480×346×235 大箱 547×407×268